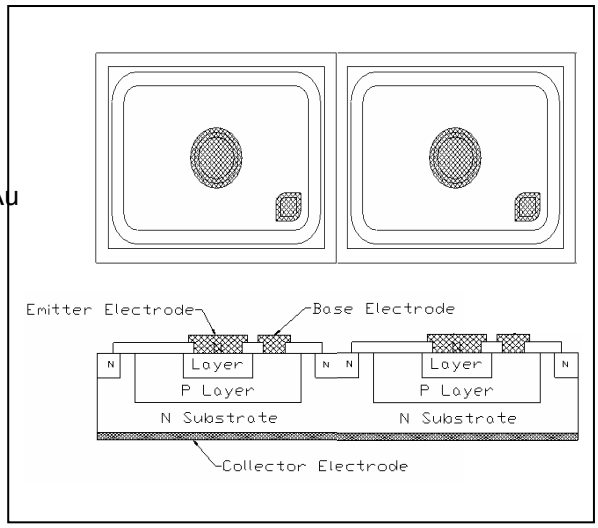
OPB1104

Silicon Photo Transistor

1. Structure

1.1 Chip Size : 0.42mm X 1.17mm
1.2 Chip thickness : 280±20um
1.3 Metallization : Top - Al, Bottom - Au
1.4 Passivation : Silicon Nitride
1.5 Bonding Pad Size
- Emitter : 130um
- Base : 60um X 60um
1.6 Active Area : 0.31mm X 0.46mm



2. Guaranteed Probed Electrical Characteristics

(Ta=25℃)

Parameter	Symbol	Min	Typ	Max	Unit	Condition
C-E Leakage Current	I_{CEO}			100	nA	V_{CE}=10V
Spectrum Sensitivity	λ	450		1100	nm	
Peak Sensing Wavelength	λp		880		nm	
C-E Voltage	BV_{CEO}	30			V	I_{CE}=500uA
C-B Voltage	BV_{CBO}	40			V	I_{CB}=50uA
E-B Voltage	BV_{EBO}	6			V	I_{EB}=50uA
E-C Voltage	BV_{ECO}	5			V	I_{EC}=50uA
C-E Saturation Voltage	V_{CES}			300	mV	I_C=5mA, I_B=1mA
DC Current Gain	h_{FE}	500		2500	-	V_{CE}=10V, Ic=1mA

3. Hfe Bin Grade

Bin Grade	MIN	MAX
A	500	1,000
B	800	1,400
C	1,300	2,500

4. Maximum Ratings

(Ta=25℃)

Parameter	Symbol	Rating	Unit
Collector-Emitter Voltage	V_{CEO}	30	V
Emitter-Collector Voltage	V_{ECO}	5	V

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